

ABSTRACT

The present invention provides a method for fabricating a nitride semiconductor laser device, which comprises a first step to form a multi-layered semiconductor on a substrate (101), the a multi-layered semiconductor containing at least an n-type nitride semiconductor layer (102), an active layer (105), and a p-type nitride semiconductor layer (108); a second step to expose the surfaces of the n-type nitride semiconductor layer (102) and the p-type nitride semiconductor layer (108) at different heights by selectively etching the multi-layered semiconductor; a third step to cover the surface of the multi-layered semiconductor, including the exposed surfaces of the n-type nitride semiconductor layer (102) and the p-type nitride semiconductor layer (108), with an insulating film (109) that has a thickness greater than the difference in levels between the exposed surface of the n-type nitride semiconductor layer (102) and the outermost surface of the p-type nitride semiconductor layer (108); a fourth step to flatten the surface of the insulating film (109); and a fifth step to form an n-type electrode (111) and a p-type electrode (110) that are electrically connected to the n-type nitride semiconductor layer (102) and the p-type nitride semiconductor layer (108), respectively, through the insulating film (109).

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This method makes it possible to obtain a nitride semiconductor laser device that is highly reliable and exhibits an excellent heat diffusing property.